

LED CHIP LED C630-30V

SPECIFICATION OF LED CHIP  
C630-30V  
[ Red ]

1) Commodity Type and Physical Characteristics.

- |                      |                               |                |
|----------------------|-------------------------------|----------------|
| 1. Material          | InGaAlP/GaAs                  |                |
| 2. Electrode         | Top Side P ( anode )side      | :Au Alloy/ Pad |
|                      | Bottom Side N ( cathode )side | :Au Alloy      |
| 3. Electrode Pattern |                               | Fig.1          |
| 4. Chip Size         |                               | Fig.2          |
| 5. Chip Thickness    |                               | Fig.2          |
| 6. Emission Area     |                               | Fig.2          |

2) Electro-Optical Characteristics [Ta=25°C]

| Parameters                   | Symbol | Condition | Min. | Typ. | Max. | Unit |
|------------------------------|--------|-----------|------|------|------|------|
| Forward Voltage              | Vf     | If=20mA   |      | 1.9  | 2.4  | V    |
| Reverse Current              | Ir     | Vr=5V     |      |      | 10   | uA   |
| Brightness                   | Iv     | If=20mA   | 40   | 90   |      | mcd  |
| Power Intensity              | Po     | If=20mA   | 0.7  | 1.2  |      | mW   |
| Peak Wavelength              | λ P    | If=20mA   | 620  | 630  | 640  | nm   |
| Spectral Radiation Bandwidth | Δλ     | If=20mA   |      | 20   |      | nm   |
| RiseTime                     | tr     | If=20mA   |      | 100  |      | ns   |
| FallTime                     | tf     | If=20mA   |      | 100  |      | ns   |

‡ Die shall be mounted on TO=18 gold header without resin coated.

[Unit: um]

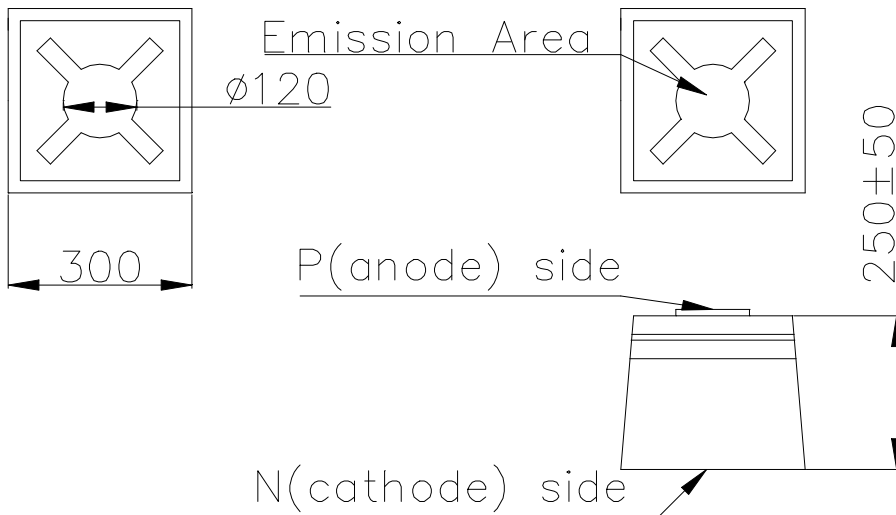


Fig.1 Electrode Pattern

Fig.2 Chip size and Emission Area